## µPD77C25/77P25 **Digital Signal Processor**

#### Description

The µPD77C25 and µPD77P25 Digital Signal Processors (DSP) are significant upgrades to the  $\mu$ PD7720—the original member of NEC's DSP family. µPD77C25 is the mask ROM version; µPD77P25 has an OTP ROM or a UVEPROM. All versions are CMOS and identical in function. Unless contextually excluded, references in this data sheet to 77C25 include 77P25

The 77C25 executes instructions twice as fast as the 77C20A/7720A, Additional instructions allow the 77C25 to execute common digital filter routines more efficiently and at more than twice the speed of a 7720 implementation.

In addition to doubled execution speed, the 77C25 has four times the instruction ROM space and twice the data ROM and RAM space of the 7720. Real savings are now possible, especially where one 77C25 can do the work of and replace two or more 7720s.

The external clock frequency (8.3 MHz maximum) remains the same as for 77C 20A/7720A while the internal instruction execution speed is doubled. For most applications, the 77C25 is plug-in compatible with the 77C20A/7720A/77P20.

The feature that distinguishes digital signal processing chips from general-purpose microcomputers is the onchip multiplier necessary for high-speed signal processing algorithms. The 77C25 multiplier is very sophisticated, especially for a low-cost DSP chip; both multiplier inputs can be loaded simultaneously from two separate memory areas. These loading operations are only two of nine operations that can occur during one 122-ns instruction cycle.

For a typical DSP filter application involving many successive multiplications, the 77C25 provides a new multiplication product for addition to a sum of products every 122 nanoseconds. Additionally, during the same instruction, memory data pointers are manipulated, and even a return from subroutine may be executed. Table 1 compares 77C25 with 77C20A.

#### Features

- Low-power CMOS: 25 mA typical current use (77C25)
- Fast instruction execution: 122 ns with 8.192-MHz clock
- All instructions execute in one instruction cycle

- Drop-in compatible with 77C20A/7720A/77P20
- 16-bit data word
- Multioperation instructions for fast program execution: any part, any combination, or all of the following operations may constitute one instruction that executes in 122 ns.
  - Load one multiplier input
  - Load the other multiplier input
  - Multiply (automatic)
  - Load product to output registers (automatic)
  - Add product to accumulator
  - Move RAM column data pointer
  - Move RAM row pointer
  - Move data ROM pointer
  - Return from subroutine
- Modified Harvard architecture with three separate memory areas
  - Instruction ROM (2048 x 24 bits)
  - Data ROM (1024 x 16 bits)
  - Data RAM (256 x 16 bits)
- □ 16 x 16-bit multiplier: 31-bit product with every instruction
- Dual 16-bit accumulators
- External maskable interrupt
- Four-level stack for subroutines and/or interrupt
- Multiple I/O capabilities
  - Serial: 8 or 16-bit (244 ns/bit)
  - Parallel: 8 or 16-bit
- Compatible with most microprocessors, including:
  - $-\mu PD8080$
  - --- μPD8085
  - µPD8086/88
  - μPD780 (Z80®)
  - µPD78xx family
- Packages: 28-pin DIP, 32-pin SOP, 44-pin PLCC
- Single + 5-volt power supply

Z80 is a registered trademark of Zilog Corporation.

#### Applications

- Portable telecommunications equipment
- Digital filtering
- High-speed data modems
- Fast Fourier transforms (FFT)

- Speech synthesis and analysis
- Dual-tone multifrequency (DTMF) transmitters/ receivers
- Equalizers

1 2 3 4 4 5 W . W

- Adaptive control
- Numerical processing

#### Performance Benchmarks

- $\square$  Second-order digital filter (biquad): 1.1  $\mu$ s
- □ Sin/cos of angles: 2.58 µs
- μ-law or A-law to linear conversion: 0.24 μs
- - 32-point complex: 0.35 ms - 64-point complex: 0.8 ms

#### Ordering Information

Part Number	Package	ROM	Operating Temperature Range -40 to +85°C	
μPD77C25C-xxx	28-pin plastic DIP	Mask		
C25GW-xxx	32-pin SOP			
C25L-xxx	44-pin PLCC			
μPD77P25C	28-pin plastic DIP	OTP	-10 to +70 °C	
P25D	28-pin ceramic DIP	UVEPROM	•	
P25GW	32-pin SOP	OTP	•	
P25L	44-pin PLCC	OTP	-	

Table 1. Comparison of 77C25 With 77C20A

	77C25/77P25	77C20A/77P20
Technology	CMOS/CMOS	CMOS/NMOS
Instruction cycle	122 ns	244 ns
Instruction ROM	2048 x 24 bits	512 x 23 bits
Data ROM	1024 x 16 bits	510 x 13 bits
Data RAM	256 x 16 bits	128 x 16 bits
Fixed-point multiplier	16 bits x 16 bits → 31 bits	16 bits x 16 bits → 31 bits
ALU	16-bit fixed-point	16-bit fixed-point
Accumulator	2 x 16 bits	2 x 16 bits
Host CPU interface	8-bit bus	8-bit bus
Serial interface	One input and one output	One input and one output
	4 MHz	2 MHz
Temporary registers	Two	One

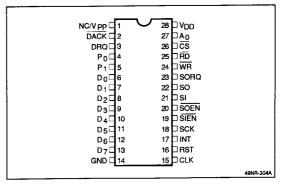
Table 1. Comparison of 77C25 With 77C20A (cont)

	77C25/77P25	77C20A/77P20
Additional	JDPLN0	
instructions	JDPLNF	_
	Modification of RAM column data pointer M8-MF	
DMA mode	Fully implemented	Partially implemented
Package	28-pin DIP	28-pin DIP
	44-pin PLCC	44-pin PLCC
	32-pin SOP	_
Power supply	5 V	5 V
Power consumption	50 mA (max) @ 8.192 MHz	40 mA (max) @ 8.192 MHz
Power saving mode (when idle)	Yes	No

Since the 77C25 executes an instruction in one external clock cycle (versus two cycles of the same 8.192-MHz clock for 77C20A), the 77C25 may be substituted for a 77C20A (or 7720A or 77P20) in a circuit without modification of that circuit. Hardware/software that implements data transfers—both serial and parallel between the 77C25 and other devices in an existing 7720 design should use the handshake protocol described in the 77C25 User's Manual.

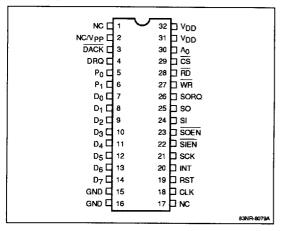
#### **Pin Configurations**

#### 28-Pin DIP

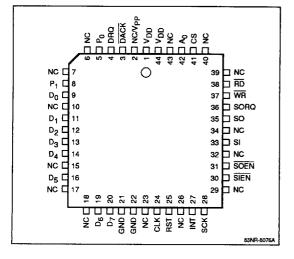


#### Pin Configurations (cont)

#### 32-Pin SOP



#### 44-Pin PLCC



#### Pin Identification

Symbol	Function			
A <sub>0</sub>	Status/data register select input			
CLK	Single-phase master clock input			
CS	Chip select input			
D <sub>0</sub> -D <sub>7</sub>	Three-state I/O data bus			
DACK	DMA request acknowledge input			
DRQ	DMA request output			
INT	Interrupt input			
P <sub>0</sub> , P <sub>1</sub>	General-purpose output control lines			
RD	Read control signal input			
RST	Reset input			
SCK	Serial data I/O clock input			
SI	Serial data input			
SIEN	Serial input enable input			
so	Three-state serial data output			
SOEN	Serial output enable input			
SORQ	Serial data output request			
WR	Write control signal input			
GND	Ground			
V <sub>DD</sub>	+5 V power supply			
NC/V <sub>PP</sub>	77C25: no connection 77P25: +12.5 V programming 77P25: +5 V for normal operation			

#### **PIN FUNCTIONS**

#### A<sub>0</sub> (Status Data Register Select)

This input selects data register for read/write (low) or status register for read (high).

#### CLK

This is the single-phase master clock input.

#### CS (Chip Select)

This input enables data transfer through the data port with RD or WR.

#### D<sub>0</sub>-D<sub>7</sub> (Data Bus)

This three-state I/O data bus transfers data between the data register or status register and the external data bus.

## DACK (DMA Request Acknowledge)

This input indicates to the 77C25 that the data bus is ready for a DMA transfer ( $\overline{DACK} = CS$  and  $A_0 = 0$ ).



#### **DRQ (DMA Request)**

This output signals that the 77C25 is requesting a data transfer on the data bus.

#### INT (Interrupt)

A low-to-high transition on this pin executes a call instruction to location 100H if interrupts were previously enabled.

## Po, P1

These pins are general-purpose output control lines.

#### RD (Read Control Signal)

This input latches data from the data or status register to the data port where it is read by an external device.

#### RST (Reset)

This input initializes the 77C25 internal logic and sets the PC to 0.

#### SCK (Serial Data I/O Clock)

When this input is high, a serial data bit is transferred.

#### SI (Serial Data Input)

This pin inputs 8- or 16-bit serial data words from an external device such as an A/D converter.

#### SIEN (Serial Input Enable)

This input enables the shift clock to the serial input register.

#### SO (Serial Data Output)

This three-state port outputs 8- or 16-bit data words to an external device such as a D/A converter.

#### SOEN (Serial Output Enable)

This input enables the shift clock to the serial output register.

#### SORQ (Serial Data Output Request)

This output specifies to an external device that the serial data register has been loaded and is ready for output. SORQ is reset when the entire 8- or 16-bit word has been transferred.

## WR (Write Control Signal)

This input writes data from the data port into the data register.

#### **GND**

This is the connection to ground.

## V<sub>DD</sub> (Power Supply)

This pin is the + 5-volt power supply.

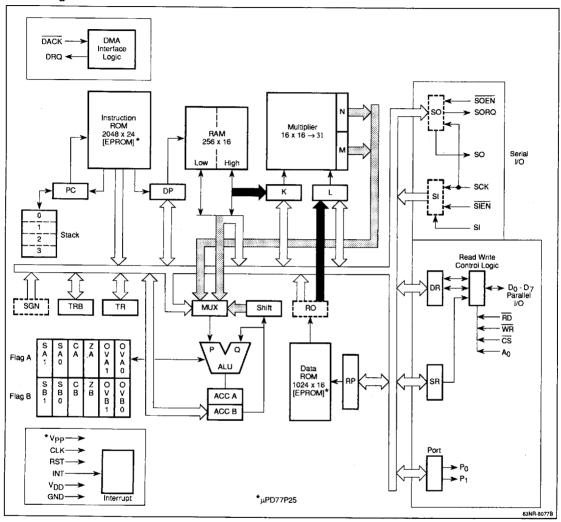
#### NC/V<sub>PP</sub>

This pin is not internally connected in the 77C25. In the 77P25, this pin inputs the programming voltage (VPP) when the part is being programmed.

This pin must be connected to V<sub>DD</sub> for normal 77P25 operation.

## μPD77C25/77P25

#### **Block Diagram**



#### **DATA BUSES**

The primary bus (unshaded in the block diagram) makes a data path between all of the registers (including I/O), memory, and the processing sections. This bus is referred to as the IDB (internal data bus). The multiplier input registers K and L can be loaded not only from the IDB but alternatively via buses (darkened in the block diagram) directly from RAM to the K register and directly from data ROM to the L register. Output from the multiplier in the M and N registers is

typically added via buses (shaded in the block diagram) to either accumulator A or B as part of a multioperation instruction.

#### **MEMORY**

Memory is divided into three types: instruction ROM, data ROM, and data RAM. The 2048 x 24-bit words of instruction ROM are addressed by an 11-bit program counter that can be modified by an external reset, interrupt, call, jump, or return instruction.



The data ROM is organized in 1024 x 16-bit words that are addressed through a 10-bit ROM pointer (RP register). The RP may be modified simultaneously with arithmetic instructions so that the next value is available for the next instruction. The data ROM is ideal for storing the necessary coefficients, conversion tables, and other constants for signal and math processing.

The data RAM is 256 x 16-bit words and is addressed through an 8-bit data pointer (DP register). The DP has extensive addressing features that operate simultaneously with arithmetic instructions, eliminating additional time for addressing or address modification.

#### ARITHMETIC CAPABILITIES

One of the unique features of the 77C25 architecture is its arithmetic facilities. With a separate multiplier, ALU, and multiple internal data paths, the 77C25 is capable of carrying out a multiply, an add or other arithmetic operation, and a data move between internal registers in a single instruction cycle.

#### ALU

The ALU is a 16-bit two's complement unit capable of executing 16 distinct operations on data routed via the P and Q ALU inputs.

#### Accumulators (ACCA/ACCB)

Associated with the ALU are two 16-bit accumulators, each with its own set of flags, which are updated at the end of each arithmetic instruction. Table 2 shows the ACC A/B flag registers. In addition to zero result, sign, carry, and overflow flags, the 77C25 incorporates auxiliary overflow and sign flags (SA1, SB1, OVA1, OVB1). These flags enable the detection of an overflow condition and maintain the correct sign after as many as three successive additions or subtractions.

Table 2. ACC A/B Flag Registers

Flag A	SA1	SAO	CA	ZA	OVA1	OVA0
Flag B	SB1	SBO	СВ	ZB	OVB1	OVB0

## Sign Register (SGN)

When OVA1 is set, the SA1 bit will hold the corrected sign of the overflow. The SGN register will use SA1 to saturation constants automatically generate 7FFFH(+) or 8000H(-) to permit efficient limiting of a calculated value. The SGN register is not affected by arithmetic operations on accumulator B, but flags SB1, SB0, CB, ZB, OVB1, and OVB0 are affected.

#### Multiplier

Thirty-one bit results are developed by a 16 x 16-bit two's complement multiplier in 122 ns. The result is automatically latched to two 16-bit registers, M and N, at the end of each instruction cycle. The sign bit and 15 higher bits are in M and the 15 lower bits are in N; the LSB in N is zero. A new product is available for use after every instruction cycle, providing significant advantages in maximizing processing speed for real-time signal processing.

#### Stack

The 77C25 contains a four-level program stack for efficient program usage and interrupt handling.

#### Interrupt

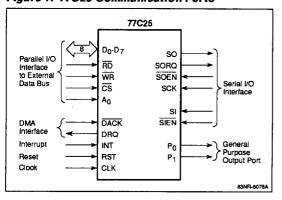
The 77C25 supports a single-level interrupt. Upon sensing a high level on the INT terminal, a subroutine call to location 100H is executed. The El bit of the status register automatically resets to 0, disabling the interrupt facility until it is reenabled under program control.

#### INPUT/OUTPUT

The 77C25 has three communication ports as shown in figure 1: two serial and one 8-bit parallel, each with its own control lines for interface handshaking. Parallel port operation is software-configurable to be in either polled mode or DMA mode. A general-purpose, twoline output port rounds out a full complement of interface capability.

#### Serial I/O

The two shift registers (SI, SO) are softwareconfigurable to single- or double-byte transfers. The shift registers are externally clocked (SCK) to provide a simple interface between the 77C25 and serial peripherals such as A/D and D/A converters, codecs, or other 77C25's. Figure 2 shows serial I/O timing



#### Parallel I/O

The 8-bit parallel I/O port may be used for transferring data or reading the 77C25 status as shown in table 3. Data transfer is handled through a 16-bit data register (DR) that is software-configurable for double- or singlebyte data transfers. The port is ideally suited for operating with 8080, 8085, and 8086 processor buses and may be used with other processors and computer systems.

#### **DMA Mode Option**

Parallel data transfers may be controlled (optionally) via DMA control lines DRQ and DACK, DMA mode allows high-speed transfers and reduced processor overhead. When in DMA mode, DACK input resets DRQ output when data transfer is completed.

Note: The RQM bit of the status register is affected by read/write operations in DMA mode the same as non-DMA mode. (In 7720 operation, RQM is not affected when in DMA mode.)

Table 3. Parallel R/W Operation

cs	Ao	WR	RD	Operation
1	Х	Х	х	No effect on internal operation; D <sub>0</sub> -D <sub>7</sub> are
X	Х	1	1	at high impedance levels.
0	0	0	1	Data from D <sub>0</sub> -D <sub>7</sub> is latched to DR (Note 1)
0	0	1	0	Contents of DR are output to D <sub>0</sub> -D <sub>7</sub> (Note 1)
0	1	0	1	lilegal (SR is read only)
0	1	1	0	Eight MSBs of SR are output to D <sub>0</sub> -D <sub>7</sub>
0	Х	0	0	Illegal (may not read and write simultaneously)

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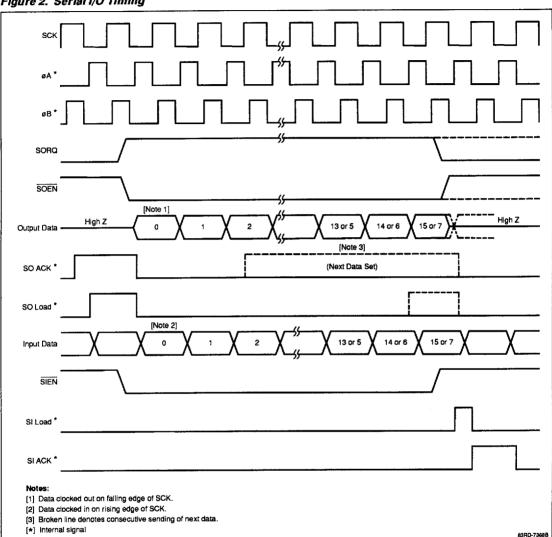
(1) Eight MSBs or LSBs of data register (DR) are used, depending on DR status bit (DRS). The condition of DACK = 0 is equivalent to  $A_0 = CS = 0.$ 

## Status Register

The status register, (figure 3, table 4) is a 16-bit register in which the 8 most significant bits may be read by the system's microprocessor for the latest parallel data I/O status. The RQM and DRS bits can only be affected by parallel data moves. The other bits can be written to (or read) by the 77C25 load immediate (LD) or move (MOV) instruction. The El bit is automatically reset when an interrupt is serviced.







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15	14	13	12	11	10	9	8
RQM	USF1	USF0	DRS	DMA	DRC	soc	SIC
MSB				·			
7	6	5	4	3	2	1	0
EI	0	0	0	0	0	P1	P0
							LSB

Table 4. Status Register Flags

Flag	Description
RQM (Request for master)	A read or write from DR to IDB sets RQM = 1. An external read (write) resets RQM = 0.
USF1 and USF0 (User flags 1 and 0)	General-purpose flags that may be read by an external processor for user-defined signaling
DRS (DR status)	For 16-bit DR transfers (DRC = 0). DRS = 1 after the first 8 bits have been transferred. DRS = 0 after all 16 bits have been transferred.
DMA (DMA enable)	DMA = 0 (Non-DMA transfer mode) DMA = 1 (DMA transfer mode)
DRC (DR control)	DRC = 0 (16-bit mode) DRC = 1 (8-bit mode)
SOC (SO control)	SOC = 0 (16-bit mode) SOC = 1 (8-bit mode)
SIC (SI control)	SIC = 0 (16-bit mode) SIC = 1 (8-bit mode)
El (Enable interrupt)	EI = 0 (interrupts disabled) EI = 1 (interrupts enabled)
P1, P0 (Ports 0 and 1)	P0 and P1 directly control the state of output pins P <sub>0</sub> and P <sub>1</sub>

#### Temporary Registers

The 77C25 has two 16-bit temporary registers.

#### INSTRUCTIONS

The 77C25 has three types of instructions: OP/RT (operation/return), JP (jump), and LD (load immediate). Each type takes the form of a 24-bit word and executes in 122 ns.

#### Instruction Timina

To control the execution of instructions, the external 8-MHz clock is divided into phases for internal execution. The various elements of the 24-bit instruction word are executed in a set order. Multiplication automatically begins first. Also, data moves from source to destination before other elements of the instruction.

Data being moved on the internal data bus (IDB) is available for use in ALU operations (if P-select field of the instruction specifies IDB). However, if the accumulator specified in the ASL field is also specified as the destination of the data move, the ALU operation becomes a NOP, as the data move supersedes the ALU operation.

Pointer modifications occur at the end of the instruction cycle after their values have been used for data moves. The result of multiplication is available at the end of the instruction cycle for possible use in the next instruction. If a return is specified as part of an OP instruction, it is executed last.

An assembly language OP instruction may consist of what looks like one to six lines of assembly code, but all of these lines are assembled together into one 24-bit instruction word. Therefore, the order of the six lines makes no difference in the order of execution described above. However, for understanding 77C25 operation and to eliminate confusion, assembly code should be written in the order described; that is: data move, ALU operations, data pointer modifications, and then return.

#### **OP/RT Instructions**

Figure 4 illustrates the OP/RT (operation/return) instruction field specification. This is really one instruction type capable of executing all ALU functions listed in table 6.

The ALU functions operate on the value specified by the P-select field (table 5).

The RT indicates an option in bit D22 that causes a return from subroutine or interrupt service.

Besides the arithmetic functions, this instruction can also (1) modify the RAM data pointer DP, (2) modify the data ROM pointer RP, and (3) move data along the on-chip data bus from a source register to a destination register. Tables 7, 8, 9, and 10 show the ASL, DPL, DPH, and RPDCR fields, respectively. The possible source and destination registers are listed in tables 11 and 12.

## NEC

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Table 5. P-Select Field

Mnemonic	D <sub>21</sub>	D <sub>20</sub>	ALU Input
RAM	. 0	0	RAM
IDB	0	1	* Internal data bus
M	1	0	M register
N	1	1	N register

<sup>\*</sup> Any value on the on-chip data bus. Value may be selected from any of the source registers listed in table 11.

Figure 4. OP/RT Instruction Field

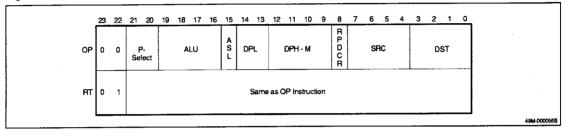


Table 6. ALU Field

Mnemonic	D <sub>19</sub>	D <sub>18</sub>	D <sub>17</sub>	D <sub>16</sub>	ALU Function	SA1, SB1	SAO, SBO	CA, CB	ZA, ZB	OVA1, OVB1	OVAO, OVBO
NOP	0	0	0	0	No operation		-				
OR	0	0	0	1	OR	×	Δ	0	Δ	0	0
AND	0	0	1	0	AND	х	Δ	0	Δ	0	0
XOR	0	0	1	1	Exclusive OR	×	Δ	0	_ Δ	0	0
SUB	0	1	0	0	Subtract	Δ	Δ	Δ	Δ	Δ	Δ
ADD	0	1	0	1	Add	Δ	Δ	Δ	Δ	Δ	Δ
SBB	0	1	1	0	Subtract with borrow	Δ	Δ	Δ	Δ	Δ	Δ
ADC	0	1	1	1	Add with carry	Δ	Δ	Δ	Δ	Δ	Δ
DEC	1	0	0	0	Decrement ACC	Δ	Δ	Δ	Δ	Δ	Δ
INC	1	0	0	1	Increment ACC	Δ	Δ	Δ	Δ	Δ	Δ
CMP	1	0	1	0	Complement ACC (one's complement)	×	Δ	0	Δ	0	0
SHR1	1	0	. 1	1	1-bit right shift	×	Δ	Δ	Δ	0	0
SHL1	1	1	0	0	1-bit left shift	×	Δ	Δ .	Δ	0	0
SHL2	1	1	0	1	2-bit left shift	×	Δ	0	Δ	0	0
SHL4	1	1	1	0	4-bit left shift	×	Δ	0	Δ	0	0
XCHG	1	1	1	1	8-bit exchange	x	Δ	0	Δ	0	0

#### Symbols:

- $\triangle\,$  May be affected, depending on the results
- Previous status can be held
- 0 Reset
- x Indefinite

#### Table 7. ASL Field

Mnemonic	D <sub>15</sub>	ACC Selection		
ACCA	0	ACCA		
ACCB	1	ACCB		

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## µPD77C25/77P25

#### Table 8. DPL Field

Mnemonic	D <sub>14</sub>	D <sub>13</sub>	Low DP Modify (DP3-DP0)
DPNOP	0	0	No operation
DPINC	0	1	Increment DPL
DPDEC	1	0	Decrement DPL
DPCLR	1	1	Clear DPL

#### Table 9. DPH Field

Mnemonic	D <sub>12</sub>	D <sub>11</sub>	D <sub>10</sub>	D <sub>9</sub>	ł
МО	0	0	0	0	E
M1	0	0	0	1	. (
M2	0	0	1	0	(
МЗ	0	0	1	1	
M4	0	1	0	0	
M5	0	1	0	1	
M6	0	1	1	0	
M7	0	1	1	1	
M8	1	0	0	0	
M9	1	0	0	1	
MA	1	0	1	0	
MB	1	0	1	1	
MC	1	1	0	0	•
MD	1	1	0	1	
ME	1	1	1	0	•
MF	1	1	1	1	•

High DP Modify Exclusive OR of DPH (DP7-DP4) with the mask defined by the 4 bits (D<sub>12</sub>-D<sub>9</sub>) of the DPH field

#### Table 10. RPDCR Field

Mnemonic	D <sub>8</sub>	RP operation
RPNOP	0	No operation
RPDEC	1	Decrement RP

Table 11. SRC Field

Mnemonic	D <sub>7</sub>	D <sub>6</sub>	D <sub>5</sub>	D <sub>4</sub>	Source Register	
NON/TRB	0	0	0	0	TRB (Note 1)	
A	0	0	0	1	ACCA (Accumulator A)	
В	0	0	1	0	ACCB (Accumulator B)	
TR	0	0	1	1	TR temporary register	
DP	0	1	0	0	DP data pointer	
RP	0	1	0	1	RP ROM pointer	
RO	0	1	1	0	RO ROM output data	
SGN	0	1	1	1	SGN sign register	
DR	1	0	0	0	DR data register	
DRNF	1	0	0	1	DR no flag (Note 2)	
SR	1	0	1	0	SR status register	

#### Table 11. SRC Field (cont)

Mnemonic	D <sub>7</sub>	D <sub>6</sub>	$D_5$	$D_4$	Source Register	
SIM	1	0	1	1	SI serial in MSB (Note 3)	
SIL	1	1	0	0	SI serial in LSB (Note 4)	
K	1	1	0	1	K register	
L	1	1	1	0	L register	
MEM	1	1	1	1	RAM	

#### Notes:

- (1) Contents of TRB register are also output if NON is specified.
- (2) DR to IDB, RQM not set. In DMA, DRQ not set.
- (3) First bit in goes to MSB, last bit to LSB.
- (4) First bit goes to LSB, last bit to MSB (bit reversed).

#### Jump Instructions

Figure 5 shows the JP instruction field specification. Bits D21, D20, and D19 of the BRCH field identify the three types of instructions: unconditional jump (100), subroutine call (101), and conditional jump (010). Table 13 lists the instruction mnemonics for the complete BRCH field, bits D<sub>21</sub>-D<sub>13</sub>.

All the instructions in table 13-if unconditional or if the specified condition is true—take their next program execution address from the next address field (NA) in figure 5. Otherwise, PC = PC + 1.

#### Load Data (LD) Instructions

Figure 6 shows the LD instruction field specification.

The load data instruction will take the 16-bit value contained in the immediate data field (ID) and place it in the register specified by the destination field (DST). This is the same as the DST field (table 12) in the OP/RT instruction.

Table 12. DST Field

Mnemonic	$D_3$	$D_2$	$D_1$	$D_0$	Destination Register
@NON	0	0	0	0	No register
@A	0	0	0	1	ACCA (Accumulator A)
@B	0	0	1	0	ACCB (Accumulator B)
@TR	0	0	1	1	TR temporary register
@DP	0	1	0	0	DP data pointer
@ RP	0	1	0	1	RP ROM pointer
@DR	0	1	1	0	DA data register
@SR	0	1	1	1	SR status register
@SOL	1	0	٥	0	SO serial out LSB (Note 1)
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Table 12. DST Field (cont)

Mnemonic	$D_3$	$D_2$	D <sub>1</sub>	Do	Destination Register
@SOM	1	0	0	1	SO serial out MSB (Note 2)
@K	1	0	1	0	K (Mult)
@KLR	1	0	1	1	IDB → K, ROM → L (Note 3)
@KLM .	1	1	0	0	Hi RAM → K, IDB → L (Note 4)
@L	1	1	0	1	L register
@TRB	1	1	1	0	TRB register

Mnemonic	$D_3$	D <sub>2</sub>	D <sub>1</sub>	D <sub>0</sub>	Destination Register
@МЕМ	1	1	1	1	RAM

#### Notes:

- (1) LSB is first bit out.
- (2) MSB is first bit out.
- (3) Internal data bus to K, and ROM to L register.
- (4) Contents of RAM address specified by DP<sub>6</sub> = 1 is placed in K register, IDB is placed in L (that is: 1, DP<sub>5</sub>, DP<sub>4</sub>, DP<sub>3</sub>-DP<sub>0</sub>).

Figure 5. JP Instruction Field Specification

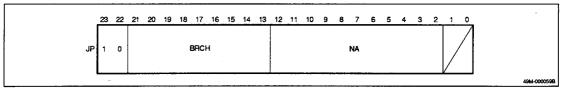


Figure 6. LD Instruction Field Specification

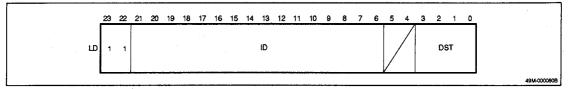


Table 13. BRCH Field

Mnemonic	D <sub>21</sub> -D <sub>19</sub>	D <sub>18</sub> -D <sub>16</sub>	D <sub>15</sub> -D <sub>13</sub>	Conditions
JMP	100	000	000	No condition
CALL	101	000	000	No condition
JNCA	010	000	000	CA = 0
JCA	0 1 0	0 0 0	0 1 0	CA = 1
JNCB	010	0 0 0	100	CB = 0
JCB	010	0 0 0	1 1 0	CB = 1
JNZA	0 1 0	0 0 1	0 0 0	ZA = 0
JZA	0 1 0	0 0 1	0 1 0	ZA = 1
JNZB	010	0 0 1	100	ZB = 0
JZB	0 1 0	0 0 1	1 1 0	ZB = 1
JNOVA0	0 1 0	0,10	000	OVA0 = 0
JOVA0	010	0 1 0	010	OVA0 = 1
JNOVBO .	0 1 0	0 1 0	1 0 0	OVB0 = 0
JOVB0	0 1 0	0 1 0	110	OVB0 = 1
JNOVA1	0 1 0	0 1 1	000	OVA1 ≈ 0
JOVA1	0 1 0	0 1 1	010	OVA1 = 1

Mnemonic	D <sub>21</sub> -D <sub>19</sub>	D <sub>18</sub> -D <sub>16</sub>	D <sub>15</sub> -D <sub>13</sub>	Conditions
JNOVB1	0 1 0	0 1 1	100	OVB1 = 0
JOVB1	0 1 0	0 1 1	1 1 0	OVB1 = 1
JNSA0	0 1 0	100	000	SA0 = 0
JSA0	0 1 0	100	010	SA0 = 1
JNSB0	0 1 0	1 0 0	100	SB0 = 0
JSB0	0 1 0	1 0 0	1 1 0	SB0 = 1
JNSA1	010	1 0 1	000	SA1 = 0
JSA1	010	1 0 1	0 1 0	SA1 = 1
JNSB1	010	1 0 1	1 0 0	SB1 = 0
JSB1	0 1 0	1 0 1	1 1 0	SB1 = 1
JDPL0	0 1 0	1 1 0	000	DPL = 0
JDPLNO	0 1 0	1 1 0	0 0 1	DPL ≠ 0
JDPLF	0 1 0	1 1 0	0 1 0	DPL = FH
JDPLNF	0 1 0	1 1 0	0 1 1	DPL ≠ FH
JNSIAK	0 1 0	1 1 0	100	SIACK = 0
JSIAK	010	1 1 0	110	SI ACK = 1

## µPD77C25/77P25

#### Table 13. BRCH Field (cont)

N E C ELECTRONICS INC

Mnemonic	D <sub>21</sub> -D <sub>19</sub>	D <sub>18</sub> -D <sub>16</sub>	D <sub>15</sub> -D <sub>13</sub>	Conditions
JNSOAK	0 1 0	1 1 1	000	SO ACK = 0
JSOAK	0 1 0	111	0 1 0	SO ACK = 1
JNRQM	0 1 0	111	1 0 0	RQM = 0
JRQM	010	1 1 1	1 1 0	RQM = 1

#### **ELECTRICAL SPECIFICATIONS**

## **Absolute Maximum Ratings**

T<sub>A</sub> = 25°C unless otherwise specified

Supply voltage, V <sub>DD</sub>	-0.5 to +7.0 V		
V <sub>PP</sub> (77P25)	-0.5 to +13.5 V		
Input voltage, V <sub>I</sub>	- 0.5 to V <sub>DD</sub> + 0.5 V		
V <sub>RST</sub> (77P25)	-0.5 to + 13 V		
Output voltage, V <sub>O</sub>	– 0.5 to V <sub>DD</sub> + 0.5 V		
Storage temperature, T <sub>STG</sub>	-65 to 150°C		
Operating temperature, T <sub>OPT</sub> 77C25/77C25-10 77P25 (Normal operation) 77P25 (PROM mode)	-40 to +80°C -10 to +70°C +20 to +30°C		

Exposure to Absolute Maximum Ratings for extended periods may affect device reliability; exceeding the ratings could cause permanent damage.

#### Recommended Operating Conditions

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Supply voltage	V <sub>DD</sub>	4.5	5.0	5.5	٧	Normal operation
		5.7	6.0	6.25	٧	Programming*
	V <sub>PP</sub> *	4.5	5.0	5.5	٧	Reading and normal operation
		12	12.5	12.8	٧	Programming
input voltage, low	V <sub>IL</sub>	-0.3		0.8	٧	
input voltage, high	V <sub>iH</sub>	2.2		V <sub>DD</sub> + 0.3	٧	•
CLK input voltage, low	V <sub>ILC</sub>	-0.3		0.5	٧	-
CLK input voltage, high	VIHC	3.5		V <sub>DD</sub> + 0.3	٧	•
Input voltage for setting PROM mode	V <sub>RST</sub> *	11.5	12.0	12.5	٧	Reading and writing
Operating temperature	Торт	-40	+ 25	+85	°C	77C25/77C25-10
		-10	+ 25	+70	°C	Normal operation*
		+20	+ 25	+30	°C	PROM mode*

<sup>\*</sup> For μPD77P25



DC Characteristics, Normal

 $T_A = -40$  to  $+85^{\circ}$ C (77C25/77C25-10), -10 to 70°C (77P25);  $V_{DD} = 4.5$  to 5.5 V

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Output voltage, low	VoL			0.45	٧	I <sub>OL</sub> = 2.0 mA
Output voltage, high	V <sub>OH</sub>	0.7 V <sub>DD</sub>			٧	$I_{OH} = 400 \mu A$
Input leakage current, low	ILIL			-10	μΑ	V <sub>IN</sub> = 0 V
Input leakage current, high	l <sub>LIH</sub>			10	μА	V <sub>IN</sub> = V <sub>DD</sub>
Output leakage current, low	ILOL			-10	μΑ	V <sub>OUT</sub> = 0.47 V
Output leakage current, high	l <sub>LOH</sub>			10	μΑ	$V_{OUT} = V_{DD}$
Supply current (77C25)	IDD		25	50	mA	f <sub>CLK</sub> = 8.192 MHz
			15	25	mA	f <sub>CLK</sub> = 8.192 MHz; RST = 1
Supply current (77P25)	1 <sub>DD</sub>		35	60	mA	f <sub>CLK</sub> = 8.192 MHz
			20	35	mA	f <sub>CLK</sub> = 8.192 MHz; RST = 1
	Ірр			1	mA	

## DC Characteristics, PROM Mode

 $T_A = +20 \text{ to } +30^{\circ}\text{C}; V_{DD} = 5.75 \text{ to } 6.25 \text{ V}$ 

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Input leakage current	I <sub>RST</sub>			30	μΑ	V <sub>RST</sub> = 12.0 ± 0.5 V
Supply current	loc			60	mA	
	Ірр			30	mA	•

## Capacitance

 $T_A = 25^{\circ}C; V_{DD} = 0 \text{ V}$ 

Parameter	Symbol	Тур	Max	Unit	Conditions
CLK, SCK capacitance	Сф		20	pF	fc = 1 MHz
Input capacitance	CIN		20	рF	
Output capacitance	C <sub>OUT</sub>		20	pF	



## **AC Characteristics**

 $T_A = -40 \text{ to } 85^{\circ}\text{C} (77C25/77C25-10), -10 \text{ to } +70^{\circ}\text{C} (77P25); V_{DD} = 4.5 \text{ to } 5.5 \text{ V}$ 

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Clock						
CLK cycle time	tcyc			•		Measuring at 2 V
77C25/77P25		120	122	2000	ns	
77C25-10		100	100	2000	ns	_
CLK pulse width	tcc					
77C25 77P25		55 60			ns	
77C25-10		45			ns ns	
CLK rise time	tcR			10	ns	Measuring at 1 and 3 V
CLK fall time	t <sub>CF</sub>			10	ns	
SCK cycle time	tcys					
77C25/77P25	-015	240	244		ns	
77C25-10		200	200		ns	
SCK high pulse with	tssH				-	_
77C25/77P25		100			ns	
77C25-10		80			ns	_
SCK low pulse width	tssL					
77C25/77P25 77C25-10		100 80			ns ns	
SCK rise time	•	80		20		_
SCK rise time SCK fall time	tsa			20	ns ns	-
Host Interface Timing	tsf				113	
AO, CS, DACK setup time for RD	<b>t</b>	0			ns	-
	tsar .					_
AO, CS, DACK hold time for RD	tHRA	0			ns	_
RD pulse width 77C25/77P25	twrd	120				
77C25/77P25 77C25-10		100			ns ns	
A0, CS, DACK setup time for WR	tsaw	0			ns	_
AO, CS, DACK hold time for WR		0			ns	_
<u></u>	t <sub>HWA</sub>				113	
WR pulse width 77C25/77P25	twwn	120			ns	
77C25/77F25 77C25-10		100			ns	
Data setup time for WR	tspw					<del>-</del>
77C25/77P25	¥¥U6°	100			ns	
77C25-10		80			ns	
Data hold time for WR	t <sub>HWD</sub>	0			ns	_
RD, WR recovery time	t <sub>RV</sub>					
77C25/77P25		100			ns	
77C25-10		80			ns	_
DACK hold time for DRQ	tHRQA	0.5t <sub>CYC</sub>			ns	
RD, WR setup time for CLK	tsrwc	50			ns	Note 1
RD, WR hold time for CLK	tHCRW	50			ns	Note 1
Host Interface Switching						
RD ↓ → data delay time	t <sub>DRD</sub>			400		
77C25/77P25				100	ns	
77C25-10				80	ns	

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AC	Characteristics (	(cont)
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Parameter	Symbol	Min	Тур	Max	Unit	Conditions
RD f → data float time	t <sub>FRD</sub>					
77C25/77P25		10		65	ns	
77C25-10		10		50	ns	and .
CLK f → DRQ delay time	<sup>t</sup> DCRQ			80		
77C25/77P25 77C25-10				65	ns ns	
	<b>4</b>					<del>-</del>
DACK ↓ → DRQ delay time 77C25/77P25	<sup>†</sup> DARQ			110	ns	
77C25-10				90	ns	
CLK 1 → P <sub>0</sub> , P <sub>1</sub> delay time	t <sub>DCP</sub>					_
77C25/77P25				100	ns	
77C25-10				80	ns	·····
Interrupt Reset Timing						
RST setup time for CLK	tsrsc					Note 1
77C25/77P25 77C25-10		50 40			ns ns	
		40	·····			Maria d
RST hold time for CLK 77C25/77P25	<sup>t</sup> HCRS	50			ns	Note 1
77C25-10		40			ns	
RST pulse width	t <sub>RST</sub>	2t CYC	•		ns	System reset
, i	1101	3t <sub>CYC</sub>			ns	Enter power saving state
NT setup time for CLK	tsinc					Note 1
77C25/77P25	51140	50			ns	
77C25-10		40			ns	
NT hold time for CLK	tHCIN					Note 1
77C25/77P25 77C25-10		50 40			ns ns	
					ns	
INT pulse width	t <sub>INT</sub>	3t <sub>CYC</sub>			ns	_
INT recovery time	<sup>t</sup> RINT	2t <sub>CYC</sub>			115	
Interrupt Reset Switching						
CLK↑ → reset state delay time 77C25/77P25	†DCRS			100	ns	
77C25-10				80	ns	
Serial Interface Timing						
SIEN, SI setup time for SCK	tssis					
77C25/77P25		50			ns	
77C25-10		40			ns	_
SIEN, SI hold time for SCK	<sup>t</sup> HSSI	20				
77C25/77P25 77C25-10		30 20			ns ns	
SOEN setup time for SCK	tooss				··•	_
77C25/77P25	tsses	50			ns	
77C25-10		40			ns	_
SOEN hold time for SCK	t <sub>HSSE</sub>					_
77C25/77P25		30			ns	
77C25-10		25			ns	
CLK setup time for SCK	tscs					Note 1
77C25/77P25		50 40			ns ns	
77C25-10		40			118	

#### AC Characteristics (cont)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
CLK hold time for SCK 77C25/77P25	thsc	50			ns	Note 1
77C25-10		40			ns	
SCK setup time for CLK	tssc					Note 1
77C25/77P25	***	50			ns	
77C25-10		40			ns	
SCK hold time for CLK	thcs					Note 1
77C25/77P25		50			ns	
77C25-10		40			ns	
Serial Interface Switching						
SCK ↑ → SORQ delay time	tDSSQ					
77C25/77P25		30		150	ns	
77C25-10		20		120	ns	
SCK↓ → SO delay time	tDSLSO	•				_
77C25/77P25				60	ns	
77C25-10				50	ns	
SCK ↓ → SO hold time	tHSLSO					_
77C25/77P25		0			ns	
77C25-10		0			ns	
SCK ↓ → SO float time	t <sub>FSSO</sub>					<del>-</del>
77C25/77P25				60	ns	
77C25-10				50	ns	

#### Notes:

(1) Setup and hold requirement for asynchronous signal only guarantees recognition at next CLK.

## PROM Program Timing

 $T_A = 25 \pm 5^{\circ}C$ ;  $V_{IHR} = 12.0 \pm 0.5 V$ 

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Data Read						
CE setup time for RST	<sup>t</sup> SRSCE	2		***	μs	$V_{DD} = 5.0 \pm 0.5 \text{ V}$
OE setup time for RST	<sup>t</sup> SRSOE	2			μs	$ V_{PP} = V_{DD}$
Data Read Switching						•
Address to output delay	t <sub>DAD</sub>			200	ns	$V_{DD} = 5.0 \pm 0.5 \text{ V}$
CE to output delay	t <sub>DCD</sub>			200	ns	V <sub>PP</sub> = V <sub>DD</sub>
OE to output delay	<sup>†</sup> DODR			75	ns	
OE high to output float	tFCD	0		60	ns	
Address to output hold	<sup>t</sup> HAD	0			ns	
Data Write						
CE setup time for RST	†SRSCE	2			μs	$V_{DD} = 6.0 \pm 0.25  \text{V}$
CE setup time for address	tsac	2			μs	$V_{pp} = 12.5 \pm 0.3 \text{ V}$
CE setup time for data	tspc	2			με	<del></del>
CE setup time for V <sub>PP</sub>	tsvpc	2			μs	_
CE setup time for V <sub>DD</sub>	tsvDC	2		•	μs	
OE setup time for data	tspo	2			μs	_

# NEC

## μPD77C25/77P25

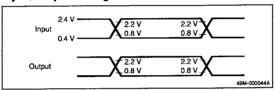
**PROM Program Timing (cont)** 

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Address hold time	t <sub>HCA</sub>	2			με	
Data hold time	tHCD	2			μs	_
Initial program pulse width	twco	0.95	1.0	1.05	ms	_
Overprogram pulse width	·two1*	2.85		78,75	ms	
Data Write Switching						
OE to output float time	t <sub>FOD</sub>	0		130	ns	$V_{DD} = 6.0 \pm 0.25 \text{ V}$
OE to output delay	†DODW			150	ns	$V_{pp} = 12.5 \pm 0.3 \text{ V}$

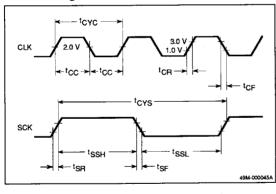
 $t_{WC1} = 3nt_{WC0}$  assuming initial program pulse is applied n times.

#### **Timing Waveforms**

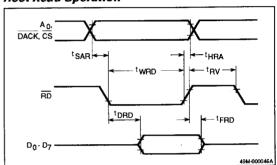
#### Input/Output Voltage Reference Levels



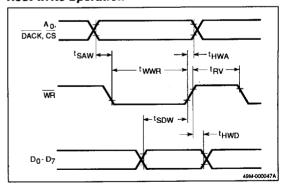
#### **Clock Timing**



#### Host Read Operation



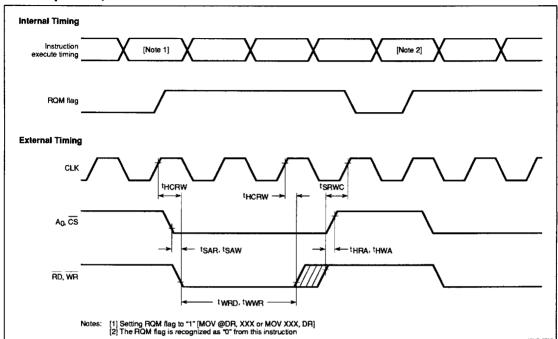
## Host Write Operation





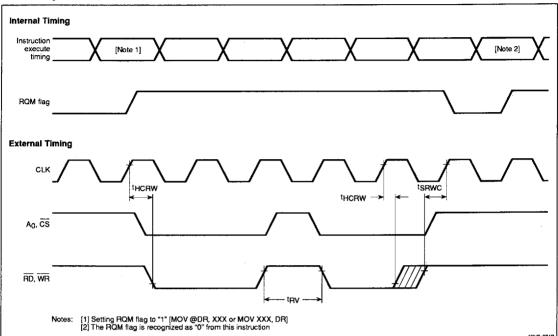
## µPD77C25/77P25

#### Normal Operation, 8-Bit Mode

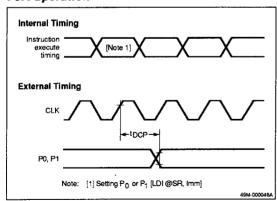




#### Normal Operation, 16-Bit Mode



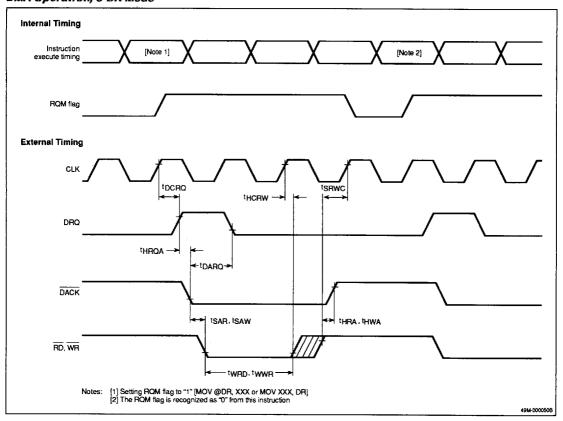
#### **Port Operation**



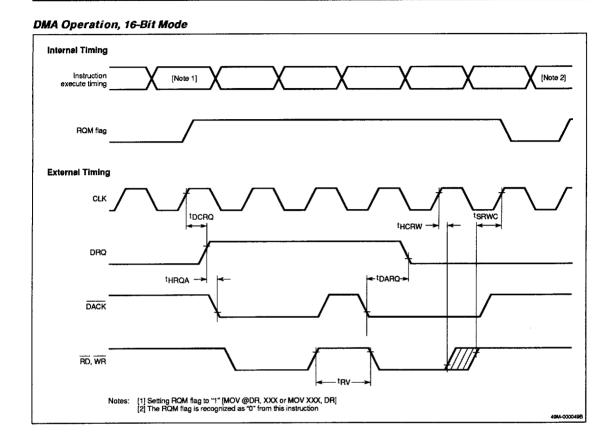
3b



## DMA Operation, 8-Bit Mode

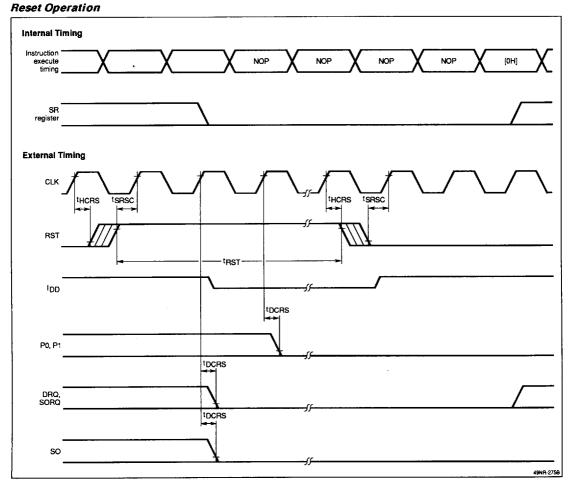










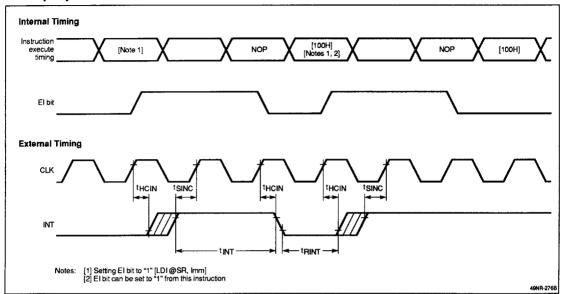


## J4 MENEC

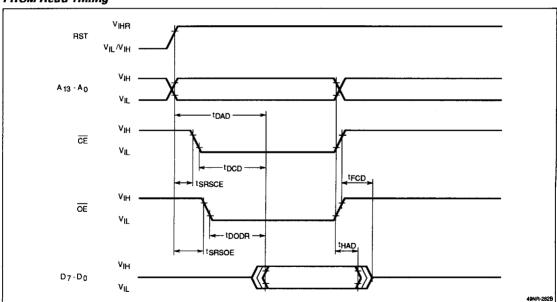
## µPD77C25/77P25



#### Interrupt Operation



## PROM Read Timing







#### **PROM Program Timing**

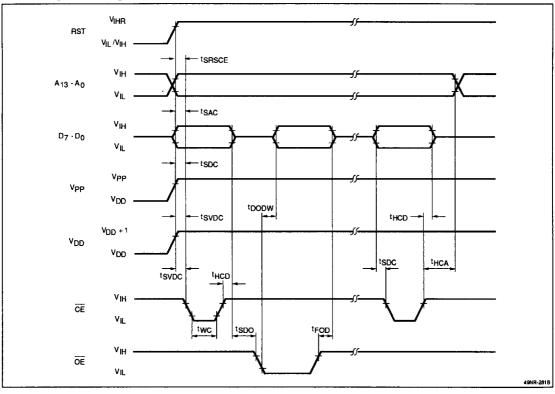
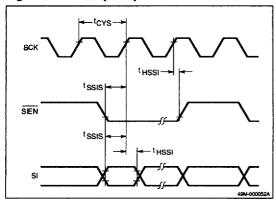


Figure 7. Serial Input Operation



#### **SERIAL TIMING**

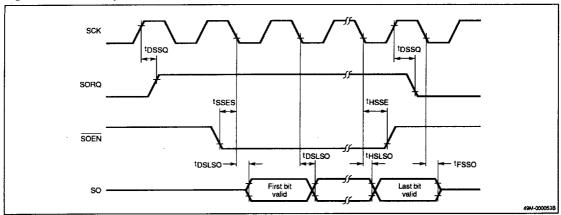
# Serial Output Case 1: SOEN Asserted in Response to SORQ

Figure 8 shows timing for serial output when SOEN is asserted in response to SORQ. If SOEN is held inactive until after SORQ is asserted, and then SOEN is asserted at least t<sub>SSES</sub> before the falling edge of SCK, SO will become valid t<sub>DSLSO</sub> after the falling edge of SCK for use by an external device at the subsequent rising edge of SCK.

Note that, although figure 8 shows  $\overline{\text{SOEN}}$  being asserted during a different SCK pulse than the one in which SORQ is asserted, it is permissible for these to occur during the same pulse of SCK as long as  $\overline{\text{SOEN}}$  is still asserted t<sub>SSES</sub> before the falling edge of SCK.

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Figure 8. Serial Output Case 1



## Serial Output Case 2: SOEN Active Before SORQ Is High

Figure 9 shows output timing when  $\overline{SOEN}$  is active before SORQ is high. If  $\overline{SOEN}$  is held active before SORQ is high, data will be shifted out whenever it becomes available in the serial output register (assuming previous data is already shifted out). In this case, SORQ will rise  $t_{DSSQ}$  after a rising edge of SCK. The first SO bit occurs  $t_{DSLSO}$  after the next falling edge of SCK for use by an external device at the subsequent rising edge of SCK.

Subsequent bits will be shifted out t<sub>DSLSO</sub> after subsequent falling edges of SCK for use at subsequent rising edges of SCK. The last bit to be shifted out will also follow this pattern, and will be held valid t<sub>FSSO</sub> after the

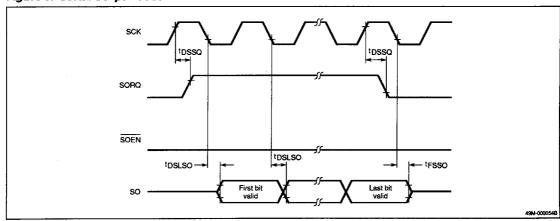
corresponding falling edge of SCK at which it is to be used. SORQ will be held  $t_{DSSQ}$  after this same rising edge of SCK, and then removed.

## Serial Output Case 3: SOEN Released During a Transfer

If  $\overline{\text{SOEN}}$  is released while SCK is in the middle of a transfer, as shown in figure 10, at least  $t_{\text{HSSE}}$  after the falling edge of SCK, then the next bit will be shifted out  $t_{\text{DSLSO}}$  after the falling edge of SCK for use at the subsequent rising edge of SCK. SO will go inactive  $t_{\text{FSSO}}$  after the falling edge of SCK.

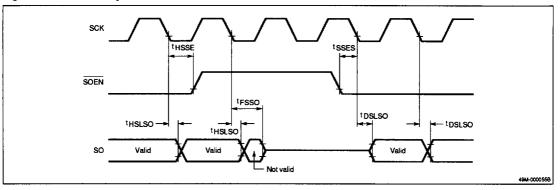
Note: For all its uses, SOEN must not change state within t<sub>SSES</sub> before or t<sub>HSSE</sub> after the falling edge of SCK; otherwise the results will be indeterminate.

Figure 9. Serial Output Case 2



μPD77C25/77P25

Figure 10. Serial Output Case 3



#### Serial Input

Serial input timing (figure 11) is much simpler than serial output timing (figure 12). Data bits are shifted in on the rising edge of SCK if SIEN is asserted. Both SIEN and SI must be stable at least t<sub>SSIS</sub> before and t<sub>HSSI</sub> after the rising edge of SCK; otherwise the results will be indeterminate.

Figure 11. Serial Input Timing Example

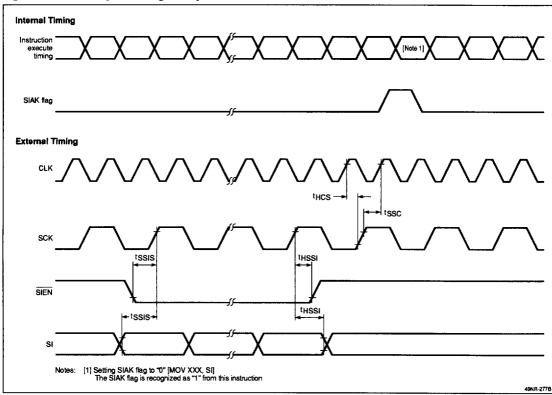
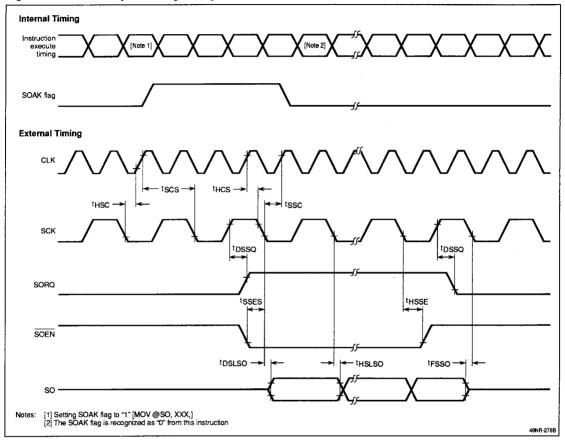




Figure 12. Serial Output Timing Example



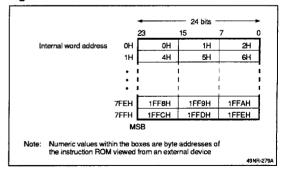
#### μPD77P25 PROM

The  $\mu$ PD77P25 has a PROM—one-time programmable (OTP) or ultraviolet erasable (UVE)—consisting of a 2K x 24-bit instruction ROM and a 1K x 16-bit data ROM.

Data is written to or read from the PROM in 8-bit bytes. Because instruction words are 24 bits and data words are 16 bits, special byte addresses are assigned to the instruction ROM (0H-1FFFH) and data ROM (2000H-27FFH) as shown in figures 13 and 14.

Each internal word address of the instruction ROM is equivalent to three byte addresses used by external devices plus one dummy byte address. For example, in figure 13, internal word address 0H corresponds to byte addresses 0H, 1H, and 2H plus dummy byte address 3H (not shown).

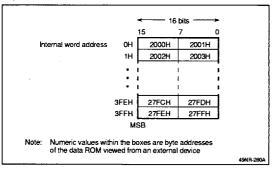
Figure 13. Instruction ROM





## µPD77C25/77P25





#### **UVEPROM Erasure**

Data in a UVEPROM can be erased by exposure to light with a wavelength shorter than 400 nm. Usually, ultraviolet light with a 254-nm wavelength is used. The erasure process, which sets all data bits to 1's, must take place before data is programmed to a UVEPROM.

The total light quantity required to completely erase the written data is 15 Ws/cm², equivalent to exposure to a UV lamp with a rating of 12,000  $\mu$ W/cm² for about 20 minutes. A longer time may be necessary because of such factors as the age of the UV lamp and stains on the package window. The window must be positioned within 1 inch of the UV lamp.

If the UVEPROM is exposed to direct sunlight or fluorescent light for a long time, the data might be destroyed. To prevent this, mask the window with a cover or film after the erasure process.

#### **Data Programming Procedure**

Following is the procedure for programming the 77P25. Table 15 shows the reassigned pin functions when writing/reading the PROM.

Since the area from byte address 2800H to 3FFFH is for internal testing, the area for the instruction ROM and data ROM must be set from byte address 0H to 27FFH. Set the data to dummy byte addresses in the instruction ROM area to FFH in the normal programming.

- Apply + 12.5 V to RST (pin 16), + 6 V to V<sub>DD</sub>, and + 12.5 V to V<sub>PP</sub>. This causes the PROM to enter program mode.
- (2) Specify the desired ROM byte address from address input pins A<sub>0</sub> to A<sub>13</sub>.
- (3) Program the data on the data bus (D<sub>0</sub>-D<sub>7</sub>) by applying 0 to CE while OE is 1 (program mode).

- (4) Output the programmed data to the data bus (D<sub>0</sub>-D<sub>7</sub>) by applying 0 to OE while CE is 1 (program verify mode).
- (5) Repeat steps 2 through 4, 25 times maximum until the data is properly written to the specified address
- (6) After verifying that the data has been properly programmed, apply additional pulses by setting OE to 1 (clear CE to 0). The pulse width is 3X ms if the number of repetitions in steps 3 and 4 is X.

The above procedure completes writing one byte of data. If the data will not be properly programmed even after steps 2 to 4 have been repeated more than 25 times, the 77P25 is defective.

Table 14. Pin Functions for PROM Programming/ Reading

Program Mode	Normal Mode	Function
A <sub>0</sub>	Α <sub>0</sub>	Input address (viewed from external device)
A <sub>1</sub>	WR	for programming/reading PROM (instruction ROM and data ROM).
A <sub>2</sub>	SORQ	Them are data from.
A <sub>3</sub>	so	•
A <sub>4</sub>	SI	•
A <sub>5</sub>	SOEN	•
A <sub>6</sub>	SIEN	•
A <sub>7</sub>	SCI	
A <sub>8</sub>	INT	•
A <sub>9</sub>	CLK	•
A <sub>10</sub>	P <sub>1</sub>	•
A <sub>11</sub>	P <sub>0</sub>	
A <sub>12</sub>	DRQ	
A <sub>13</sub>	DACK	
D <sub>0</sub> -D <sub>7</sub>	D <sub>0</sub> -D <sub>7</sub>	Input/output data for PROM (instruction ROM and data ROM)
CE	<del>CS</del>	PROM program strobe signal (active low)
ŌĒ	RD	PROM read strobe signal (active low)
V <sub>PP</sub>	V <sub>PP</sub>	Power pin for programming PROM; apply +12.5 V for writing and +5 V for reading.
V <sub>DD</sub>	V <sub>DD</sub>	Power pin; apply +6 V for programming and +5 V for reading.
GND	GND	Ground pin
	RST	Sets PROM program or read mode. Mode is set when +12.5 V is applied.



#### **Data Reading Procedure**

- Apply + 12.5 V to RST, +5.0 V to V<sub>DD</sub>, and +5.0 V to V<sub>PP</sub>. This causes the PROM to enter read mode.
- (2) Specify the desired ROM byte address from the address input pins A<sub>0</sub> to A<sub>13</sub>.
- (3) Data will be output to the data bus (D<sub>0</sub>-D<sub>7</sub>) by clearing OE and CE to 0.

#### Instruction ROM Code Protection

A word of the instruction ROM can be protected if data FEH is programmed to a dummy byte address. For example, byte addresses 0H, 1H, and 2H (word address 0H) are protected if FEH is programmed to dummy byte address 3H. Following is the procedure for protecting the instruction ROM.

- (1) Set data FFH to the dummy addresses; then perform the data program procedure.
- (2) Verify the programmed data by the data read procedure.
- (3) Set data FEH to the dummy addresses; again perform the data program procedure.

#### **DEVELOPMENT TOOLS**

For software development and assembly into object code, a relocatable assembler (RA77C25) is available. This software is available to run on MS-DOS®, CP/M®, VAX®/VMS®, and VAX/UNIX® systems.

For debugging, a hardware emulator (EVAKIT-77C25) provides in-circuit, real-time emulation of the 77C25. Features of the EVAKIT-77C25 include break/step emulation, symbolic debugging, and on-line assembly/ disassembly of code.

The EVAKIT-77C25 connects via a probe to the target system for test and demonstration of the final system design. It also connects to the host development system via an RS-232 port. Using Kermit or NEC's EVA communications program, code can be downloaded or uploaded between development system and EVAKIT.

By connecting to a PROM programmer, the EVAKIT is also used to prepare 77P25 PROMs intended for prototyping and small volume applications. A program adaptor, PA-77P25, is provided for use with the data I/O programmer.

Code submittal for the mask ROM  $\mu$ PD77C25 is accomplished by preparing a 27C256A or  $\mu$ PD77P25 PROM using the same programming device.

#### SYSTEM CONFIGURATION

Figures 15, 16, 17, and 18 show typical system applications for the 77C25.

Figure 15. Spectrum Analysis System

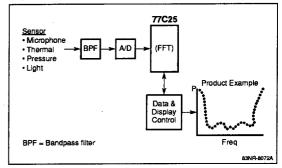
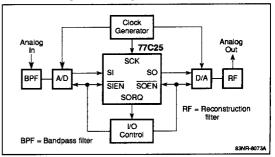


Figure 16. Analog-to-Analog Digital Processing System Using a Single 77C25



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Figure 17. Signal Processing System Using Cascaded 77C25's and Serial Communication

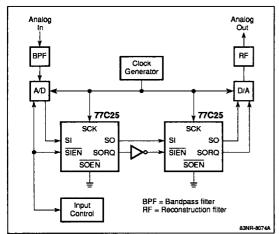
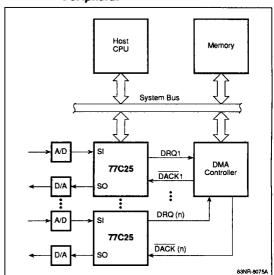


Figure 18. Signal Processing System Using 77C25's As a Complex Computer Peripheral



3b